



PNP Transistors Array

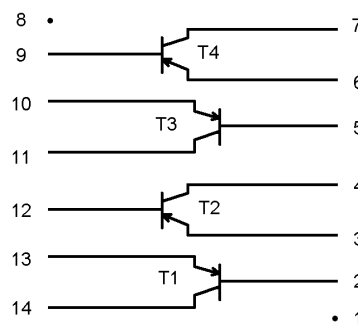
HJ622A

GENERAL DESCRIPTION

The HJ622A is a PNP Transistors Array IC, Pin to pin replaced RUSSIAN IC **2TC622A**. It not only have closely Elec-match and excellent Heat-match but also coherence and uniformity is superior to other discrete circuit. Package is Ceramic Flat 14pin, Reliability and relative stability worked in $-55^{\circ}\text{C} \sim +125^{\circ}\text{C}$.

ELECTRIC PRINCIPLE DIAGRAM

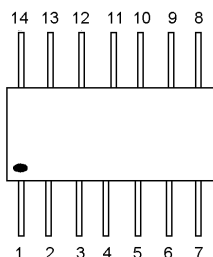
Table 1.



PKG & PIN CONFIGURATION

Table 2.

Ceramic Flat 14pin



Pin NO.	1	2	3	4	5	6	7
FUN	NC	b ₁	e ₂	c ₂	b ₃	e ₄	c ₄
Pin NO.	8	9	10	11	12	13	14
FUN	NC	b ₄	e ₃	c ₃	b ₂	e ₁	c ₁

ABSOLUTE MAXIMUM RATINGS

Voltage of Power Supply: 50V
Operating Temperature: $-55^{\circ}\text{C} \sim +125^{\circ}\text{C}$.

Dissipation Power: 600mW
Junction Temperature: $+175^{\circ}\text{C}$

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ELECTRICAL CHARATERISTICS

-55℃≤T_A≤+125℃ unless otherwise noted.

Table 3.

Parameter	Symbol	Conditions	Ratings			Unit
			Min	Typ	Max	
DC Forward-Current Transfer Ratio	h _{FE}	V _{CE} =5V, I _E =200mA	25	100	150	
Collector-Cutoff Current	I _{CBO}	V _{CB} =45V		0.1	10	A
Collector-Emitter Satiation Voltage	V _{CE(sat)}	I _B =80mA, I _C =400mA		0.2	1.3	V
Emitter - Current	I _{EBO}	V _{EB} =4V		0.1	20	A
Base- Emitter Satiation Voltage	V _{BE(sat)}	I _B =80mA			1.2	V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =0.1mA	55			V
Current-Gain Bandwidth Product	f _T	V _{CE} =10V, I _C =3mA	200			MHz

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